# **VS-22RIA Series**

### **Vishay Semiconductors**

## Medium Power Phase Control Thyristors (Stud Version), 22 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	22 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V				
V <sub>TM</sub>	1.70 V				
I <sub>GT</sub>	60 mA				
TJ	-65 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration	Single SCR				

#### FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		22	A			
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C			
I <sub>T(RMS)</sub>		35	A			
1	50 Hz	400				
ITSM	60 Hz	420	— A			
l <sup>2</sup> t	50 Hz	793	— A <sup>2</sup> s			
1-1	60 Hz	724	A-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V			
tq	Typical	110	μs			
TJ		-65 to +125	°C			

#### **ELECTRICAL SPECIFICATIONS**

#### **VOLTAGE RATINGS** V<sub>DRM</sub>/V<sub>RRM</sub>, MAXIMUM REPETITIVE PEAK V<sub>RSM</sub>, MAXIMUM NON-REPETITIVE I<sub>DRM</sub>/I<sub>RRM</sub> MAXIMUM TYPE VOLTAGE $ATT_J = T_J MAXIMUM$ AND OFF-STATE VOLTAGE (1) PEAK VOLTAGE (2) NUMBER CODE ν ν mA 10 100 150 20 20 200 300 40 400 500 VS-22RIA 60 600 700 10 80 800 900 100 1000 1100 120 1200 1300

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

<sup>(2)</sup> For voltage pulses with  $t_p \le 5$  ms

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RoHS



# **VS-22RIA Series**



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## Vishay Semiconductors

ABSOLUTE MAXIMUM RATI	SYMBOL		TEST CON		VALUES	UNITS	
PARAMETER	STMBOL	TEST CONDITIONS					
Maximum average on-state current	I <sub>T(AV)</sub>	180° sinuso	bidal conduction		22	A	
at case temperature					85	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>				35	Α	
		t = 10 ms	No voltage		400		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		420	<b>_</b>	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		335	A	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	355	-	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	793	A <sup>2</sup> s	
	10.	t = 8.3 ms	reapplied	-	724		
	l <sup>2</sup> t	t = 10 ms	100 % V <sub>BBM</sub>		560		
		t = 8.3 ms	reapplied		515		
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied, $T_J = T_J$ maximum			7930	A²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.83		
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$_{0}$ ), T <sub>J</sub> = T <sub>J</sub> maxim	um	0.95	V	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			14.9		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			13.4	mΩ	
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 70 A, T <sub>J</sub> = 25 °C			1.70	V	
Maximum holding current	Ι <sub>Η</sub>	T 05 %C	anada ayanki G	V registive lood	130		
Latching current	IL	$T_J = 25$ °C, anode supply 6 V, resistive load			200	- mA	

SWITCHING							
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS		
$V_{DRM} \le 600 \text{ V}$				200			
Maximum rate of rise of turned-on current	$V_{DRM} \leq 800 \ V$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ Gate pulse = 20 V, 15 $\Omega$ , $t_p = 6 \mu s$ , $t_r = 0.1 \mu s$ maximum $I_{TM} = (2 x rated dl/dt) A$	180	A/µs		
	$V_{DRM} \leq 1000 \ V$	ui/ui		160			
	$V_{DRM} \le 1600 \text{ V}$			150			
Typical turn-on time		t <sub>gt</sub>	$T_J = 25 \text{ °C}$ , at rated $V_{DRM}/V_{RRM}$ , $T_J = 125 \text{ °C}$	0.9			
Typical reverse recovery time		time $ \begin{array}{c} T_J = T_J \text{ maximum, } I_{TM} = I_{T(AV)},  t_p > 200 \; \mu s, \\ dI/dt = - \; 10 \; A/\mu s \end{array} $		4	μs		
Typical turn-off time		tq	$\label{eq:transform} \begin{array}{l} T_J=T_J\mbox{ maximum, } I_{TM}=I_{T(AV)},\ t_p>200\ \mu s,\ V_R=100\ V,\\ dI/dt=-\ 10\ A/\mu s,\ dV/dt=20\ V/\mu s\ linear\ to\ 67\ \%\ V_{DRM},\\ gate\ bias\ 0\ V\ to\ 100\ W \end{array}$	110	μo		

#### Note

•  $t_q = 10 \ \mu s$  up to 600 V,  $t_q = 30 \ \mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	100	
of off-state voltage		$T_J = T_J$ maximum linear to 67 % rated $V_{DRM}$	300 (1)	V/µs

Note

 $^{(1)}$  Available with: dV/dt = 1000 V/µs, to complete code add S90 i.e. 22RIA120S90

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TRIGGERING						
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_{i} = T_{i}$ maximum		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>	$1_{j} = 1_{j}$ maximum		2.0		
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum		1.5	А	
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V	
		T <sub>J</sub> = - 65 °C		90	mA	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger	60		
		T <sub>J</sub> = 125 °C	current/voltage are the lowest	35		
	V <sub>GT</sub>	T <sub>J</sub> = - 65 °C	value which will trigger all units	3.0	v	
DC gate voltage required to trigger		T <sub>J</sub> = 25 °C	6 V anode to cathode applied	2.0		
		T <sub>J</sub> = 125 °C		1.0		
DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		2.0	mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum,$ $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES			
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +125		°C		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.86		K/W		
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased		0.35			
			TO NUT	TO DEVICE			
			20 (27.5)	25	lbf · in		
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf∙m		
				2.8	N·m		
			14		g		
Approximate weight				0.49			
Case style		See dimensions - link at the end of datasheet	TO-48 (TO-208AA)		A)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS				
180°	0.21	0.15						
120°	0.25	0.25						
90°	0.31	0.34	$T_J = T_J maximum$	K/W				
60°	0.45	0.47						
30°	0.76	0.76						

Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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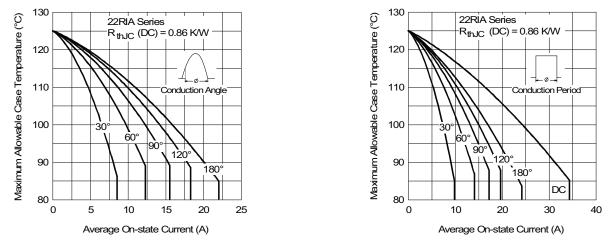
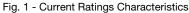
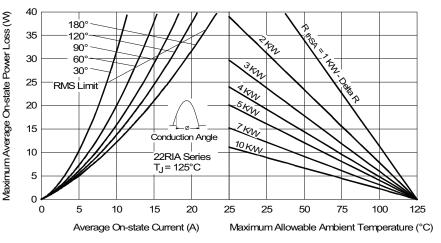


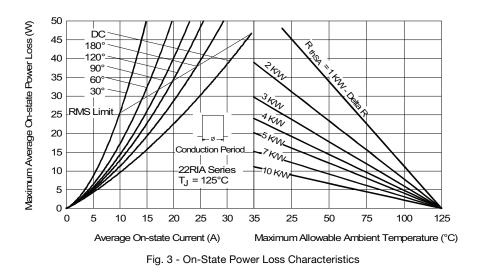
Fig. 1 - Current Ratings Characteristics

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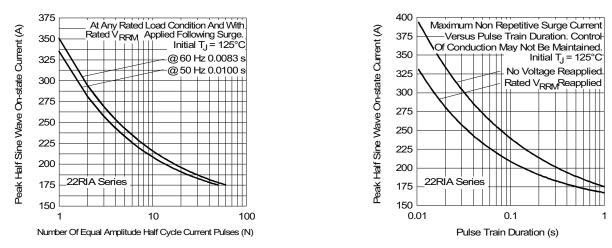


Fig. 4 - Maximum Non-Repetitive Surge Current

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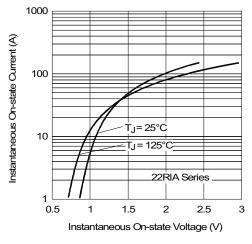
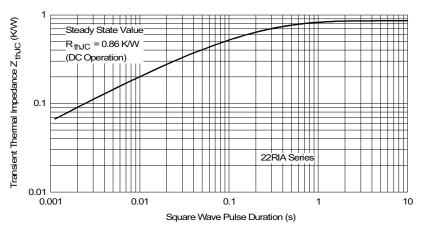
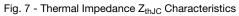


Fig. 6 - Forward Voltage Drop Characteristics





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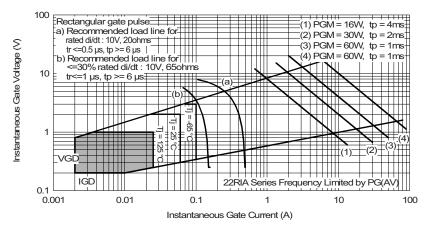


Fig. 8 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

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Device code	VS-	22	RIA	120	М	S90	
	1	2	3	4	5	6	
	1 -			nicondu	ctors pro	oduct	
	2 - 3 -		rent coo sential p	art numl	ber		
	4 - 5 -	Nor	ne = stu	d base ⊺	FO-48 (1	、 ГО-208/	Itage Ratings tab AA) 1/4" 28UNF-2 M6 x 1
	6 -	Crit Nor	ical dV/ ne = 300	ase TO-/ dt: ) V/µs (s ) V/µs (s	standard	l value)	

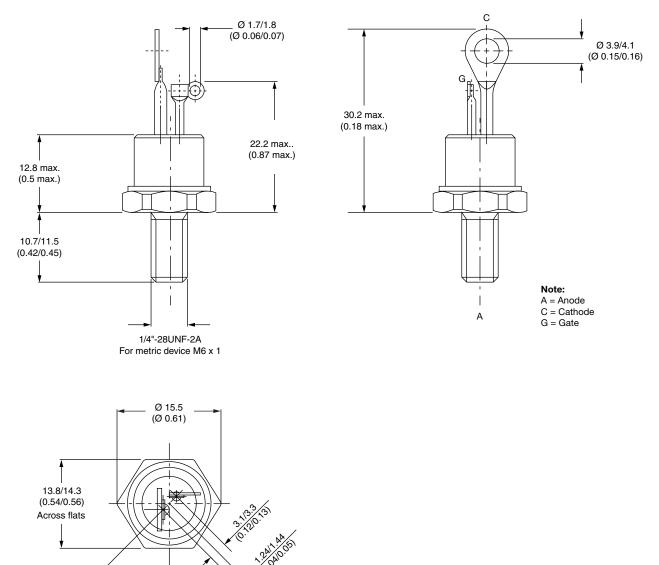
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95333			



# TO-208AA (TO-48)

#### **DIMENSIONS** in millimeters (inches)

45°





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